

FLU17ZM

L-Band Medium & High Power GaAs FET

FEATURES

- High Output Power: P1dB=32.5dBm(typ.)
- High Gain: G1dB=12.5dB(typ.)
- Low Cost Plastic(SMT) Package
- Tape and Reel Available

DESCRIPTION

The FLU17ZM is a GaAs FET designed for base station and CPE applications. This is a new product series using a plastic surface mount package that has been optimized for high volume cost driven applications. Fujitsu's stringent Quality Assurance Program assures the highest reliability and consistent performance.



ABSOLUTE MAXIMUM RATINGS (Case Temperature Tc=25°C)

Item	Symbol	Rating	Unit
Drain-Source Voltage	V _{DS}	15	V
Gate-Source Voltage	V _{GS}	-5	V
Total Power Dissipation	P _T	8.3	W
Storage Temperature	T _{stg}	-55 to +150	°C
Channel Temperature	T _{ch}	150	°C

Recommended Operating Condition (Case Temperature Tc=25°C)

Item	Symbol	Condition	Unit
DC Input Voltage	V _{DS}	≤ 10	V
Channel Temperature	T _{ch}	≤ 145	°C
Forward Gate Current	I _{gsf}	≤ 9.6	mA
Reverse Gate Current	I _{gsr}	≥ -1.0	mA
Gate Resistance	R _g	200	Ω

ELECTRICAL CHARACTERISTICS (Case Temperature Tc=25°C)

Item	Symbol	Test Conditions	Limit			Unit
			Min.	Typ.	Max.	
Drain Current	I _{DSS}	V _{DS} =5V, V _{GS} =0V	-	600	900	mA
Transconductance	gm	V _{DS} =5V, I _{DS} =400mA	-	300	-	mS
Pinch-off Voltage	V _p	V _{DS} =5V, I _{DS} =30mA	-1.0	-2.0	-3.5	V
Gate-Source Breakdown Voltage	V _{GSO}	I _{GS} =-30uA	-5	-	-	V
Output Power at 1dB G.C.P.	P1dB	V _{DS} =10V, f=2.0GHz, I _{DS} =0.6I _{DSS} (Typ.)	31.5	32.5	-	dBm
Power Gain at 1dB G.C.P.	G1dB		11.5	12.5	-	dB
Thermal Resistance	R _{th}	Channel to Case	-	12	15	°C/W

CASE STYLE: ZM

G.C.P.: Gain Compression Point

Note 1: Product supplied to this specification are 100% DC performance tested.

Note 2: The RF parameters are measured on a lot basis by sample testing 10 pcs/lot.

Acceptance Criteria:(accept/reject)=(0/1). Any lot failure shall be 100% retested.

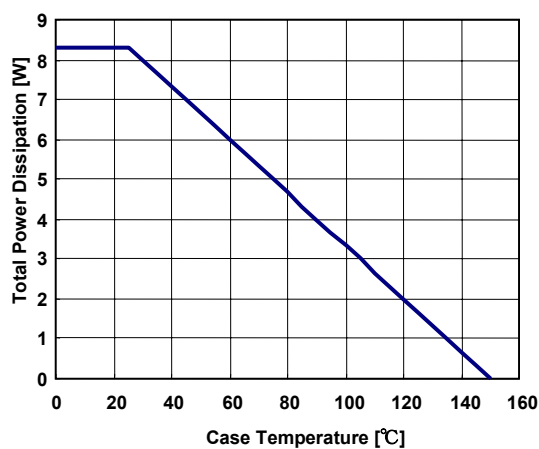
ESD	Class II	500 ~ 1999 V
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Note : Based on EIAJ ED-4701 C-111A (C=100pF,R=1.5kΩ)

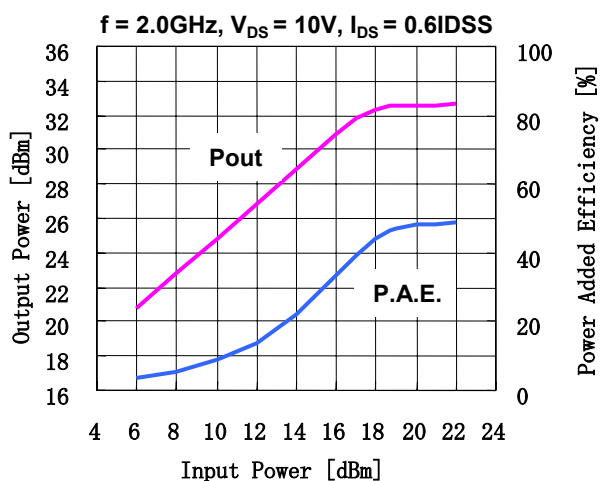
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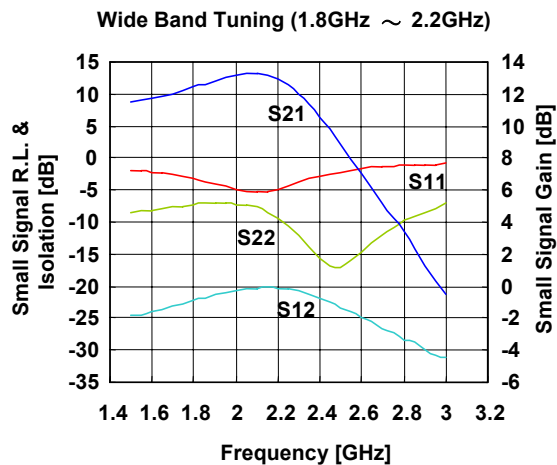
POWER DERATING CURVE



OUTPUT POWER & POWER ADDED EFFICIENCY vs. INPUT POWER



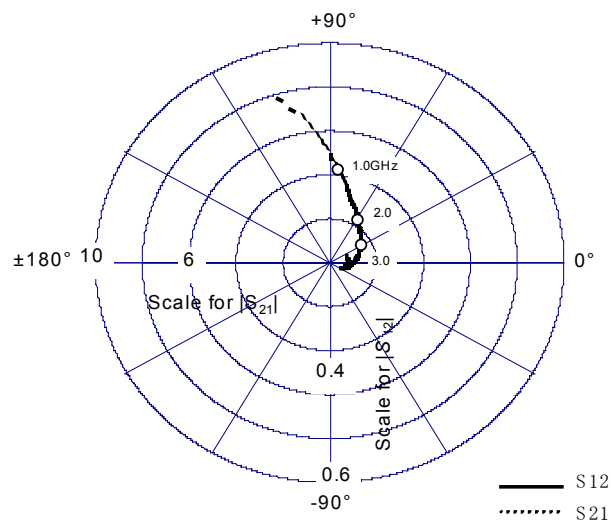
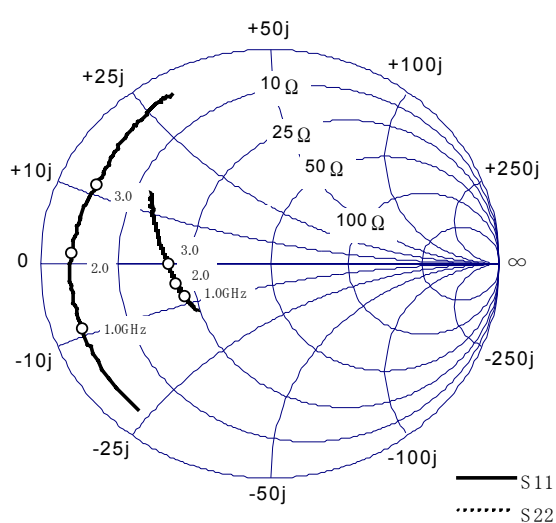
SMALL SINGLE R.L. vs FREQUENCY



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S-PARAMETER



$V_{DS} = 10V, I_{DS} = 360mA$

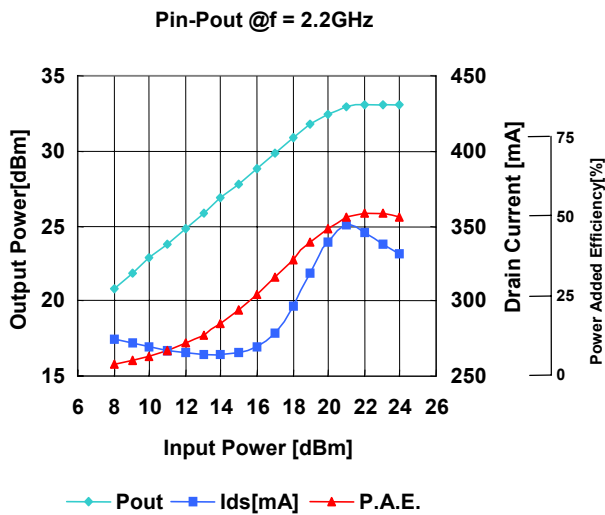
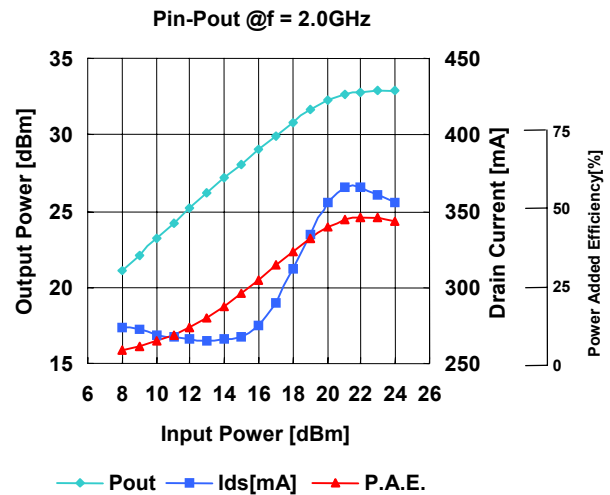
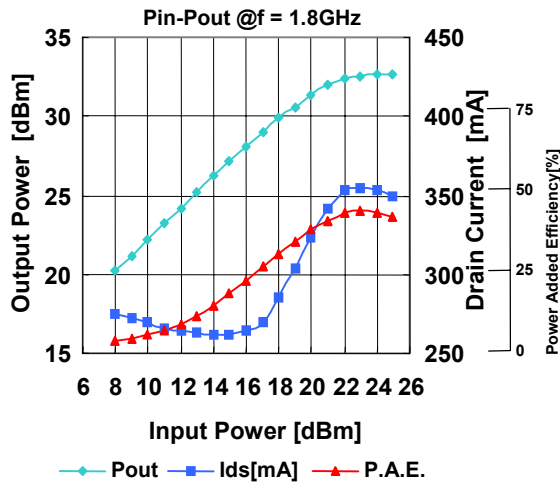
Freq [GHz]	S11		S21		S12		S22	
	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG
0.5	0.89	-130.40	7.82	106.20	0.05	22.81	0.38	-144.06
1	0.87	-159.47	4.26	84.91	0.05	10.25	0.40	-157.62
1.5	0.87	-172.30	2.95	71.11	0.05	3.23	0.41	-162.28
2	0.87	176.73	2.31	58.41	0.05	-2.81	0.42	-166.91
2.5	0.85	166.01	1.89	45.71	0.05	-10.38	0.43	-172.98
3	0.84	153.61	1.58	31.88	0.04	-11.34	0.44	179.73
3.5	0.85	142.11	1.33	18.68	0.04	-15.81	0.48	170.94
4	0.87	131.82	1.12	5.71	0.04	-20.61	0.52	162.31
4.5	0.89	124.40	0.94	-5.77	0.04	-22.32	0.57	154.52
5	0.90	118.39	0.79	-16.59	0.03	-26.62	0.61	147.78

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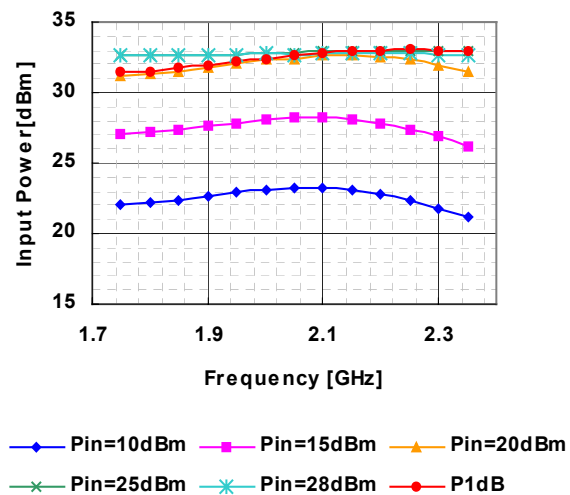
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OUTPUT POWER, DRAIN CURRENT vs. INPUT POWER

@ $V_{DS} = 10V$, $I_{DS} = 0.6I_{DSS}$



OUTPUT POWER vs. FREQUENCY

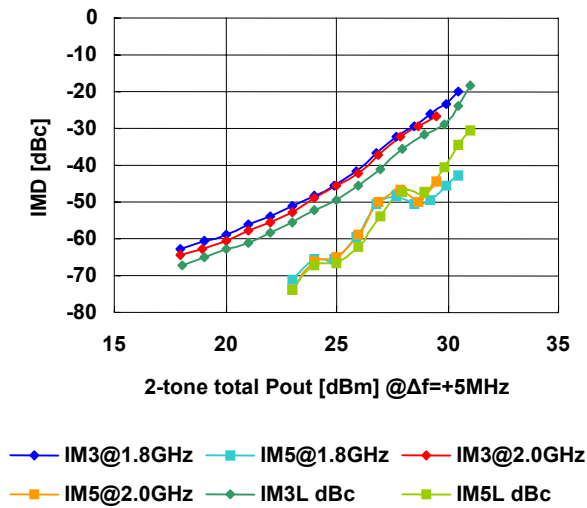


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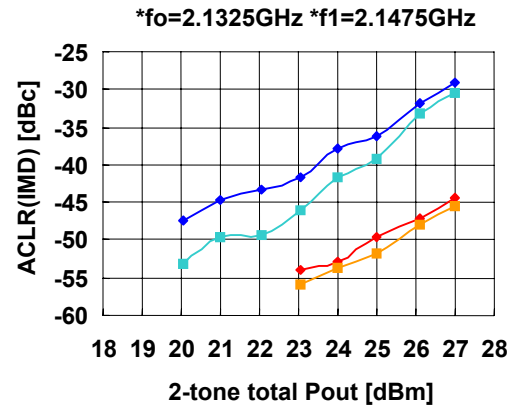
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@ $V_{DS} = 10V$, $I_{DS} = 0.6IDSS$

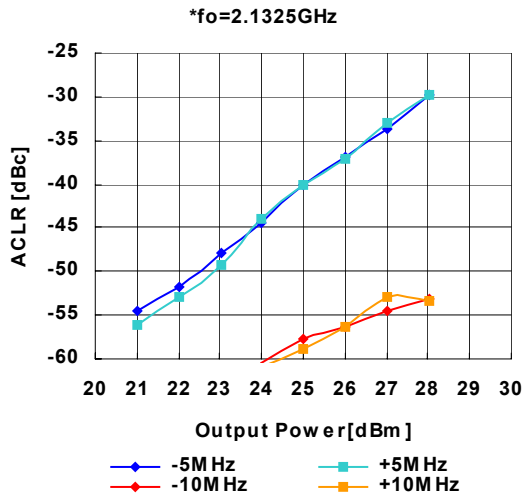
IMD vs OUTPUT POWER(2-tone)



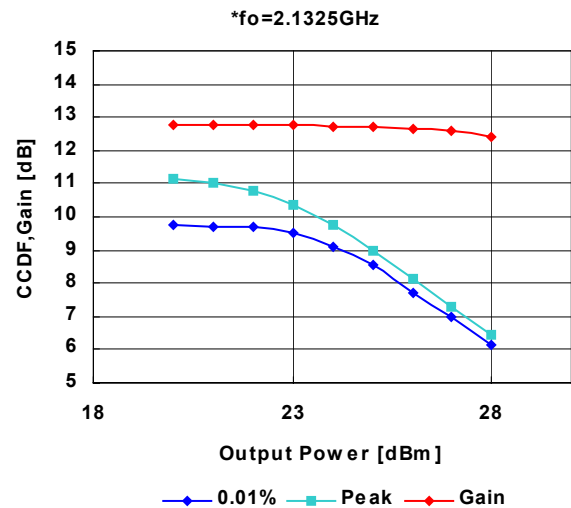
W-CDMA, 2-CARRIER IMD(ACLR)



W-CDMA SINGLE CARRIER ACLR



W-CDMA SINGLE CARRIER CCDF AND GAIN

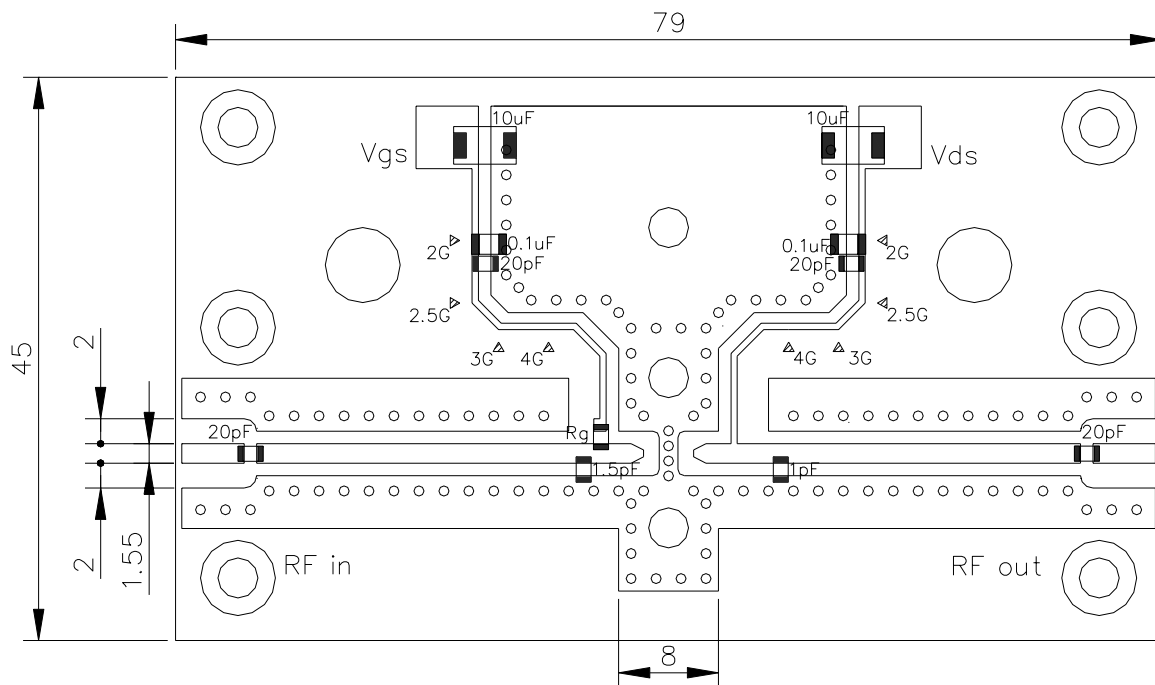


Note : *All signals are W-CDMA modulated at 3GPP3.4.12-00 BS-1 64ch non clipping.

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■ Recommended Bias Circuit and Internal Block Diagram



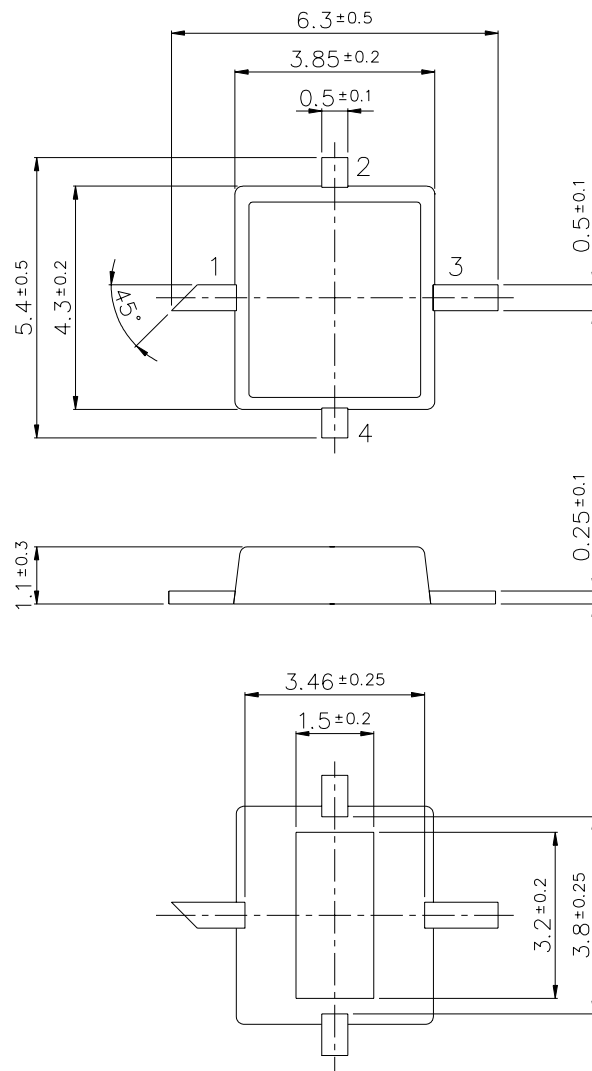
<Board information>
 $\epsilon_r=3.5$, $t=0.8$

* Board was tuned for wide band performance with data shown on pages 4 and 5.

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■ Package Outline



1 : Gate
2. Source
3. Drain
4. Source
Unit : mm

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For further information please contact :

FUJITSU COMPOUND SEMICONDUCTOR, INC.

2355 Zanker Rd.
San Jose, CA 95131-1138, U.S.A.
Phone: (408) 232-9500
FAX: (408) 428-9111
www.fcsi.fujitsu.com

FUJITSU QUANTUM DEVICES EUROPE LTD.

Network House
Norreys Drive
Maidenhead, Berkshire SL6 4FJ
Phone: +44 (0) 1628 504800
FAX: +44 (0) 1628 504888

FUJITSU QUANTUM DEVICES LIMITED

Business Development Division
11th Floor, Hachioji Daiichi-Seimei Bldg.
3-20-6 Myojin-cho
Hachioji-city, Tokyo 192-0046, Japan
TEL: +81-426-43-5885
FAX: +81-426-43-5582

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FUJITSU QUANTUM DEVICES SINGAPORE PTE LTD.

Hong Kong Branch
Rm. 1101, Ocean Centre, 5 Canton Rd.
Tsim Sha Tsui, Kowloon, Hong Kong
TEL: +852-23770226
FAX: +852-23763269

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